

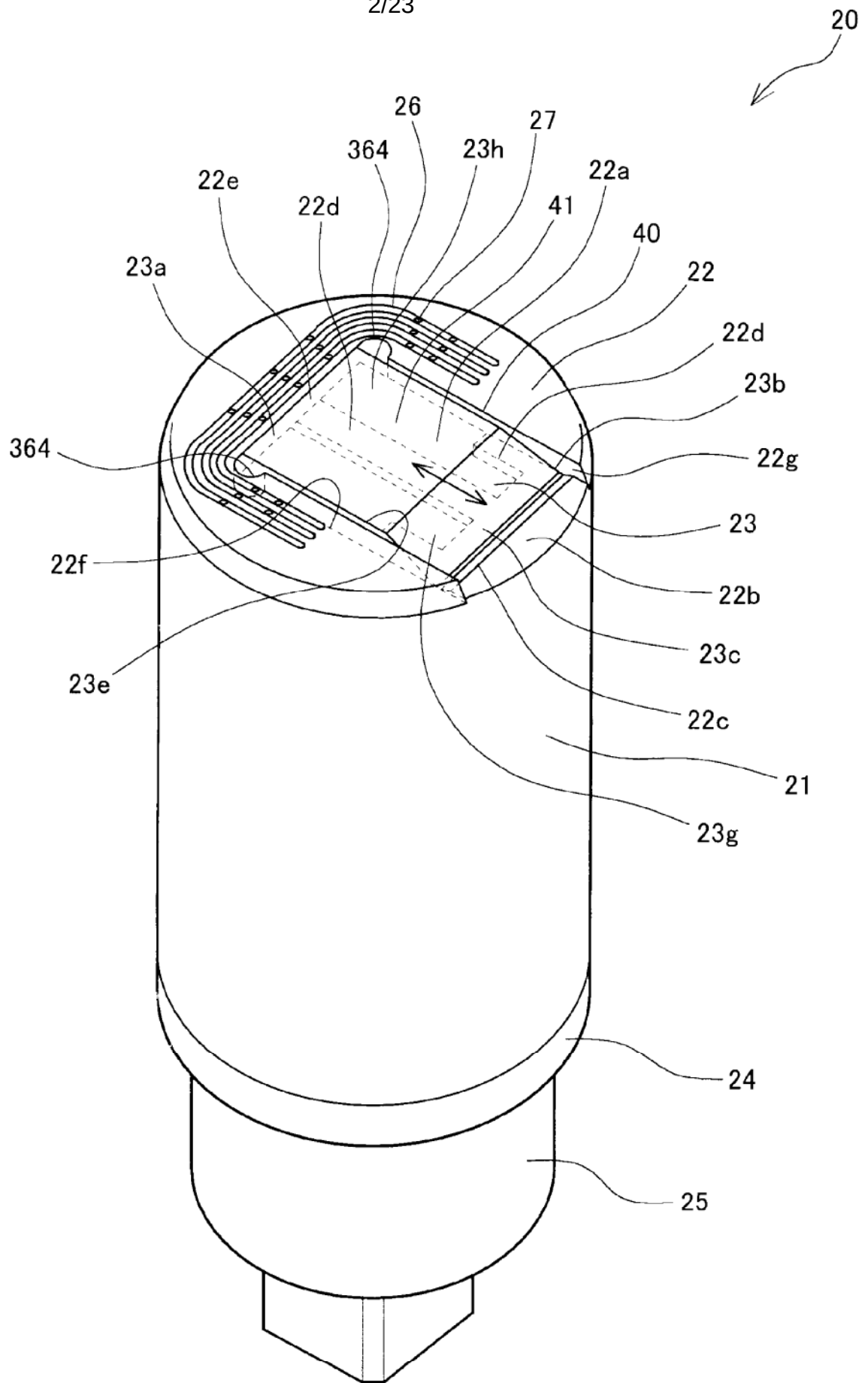


FIG. 2

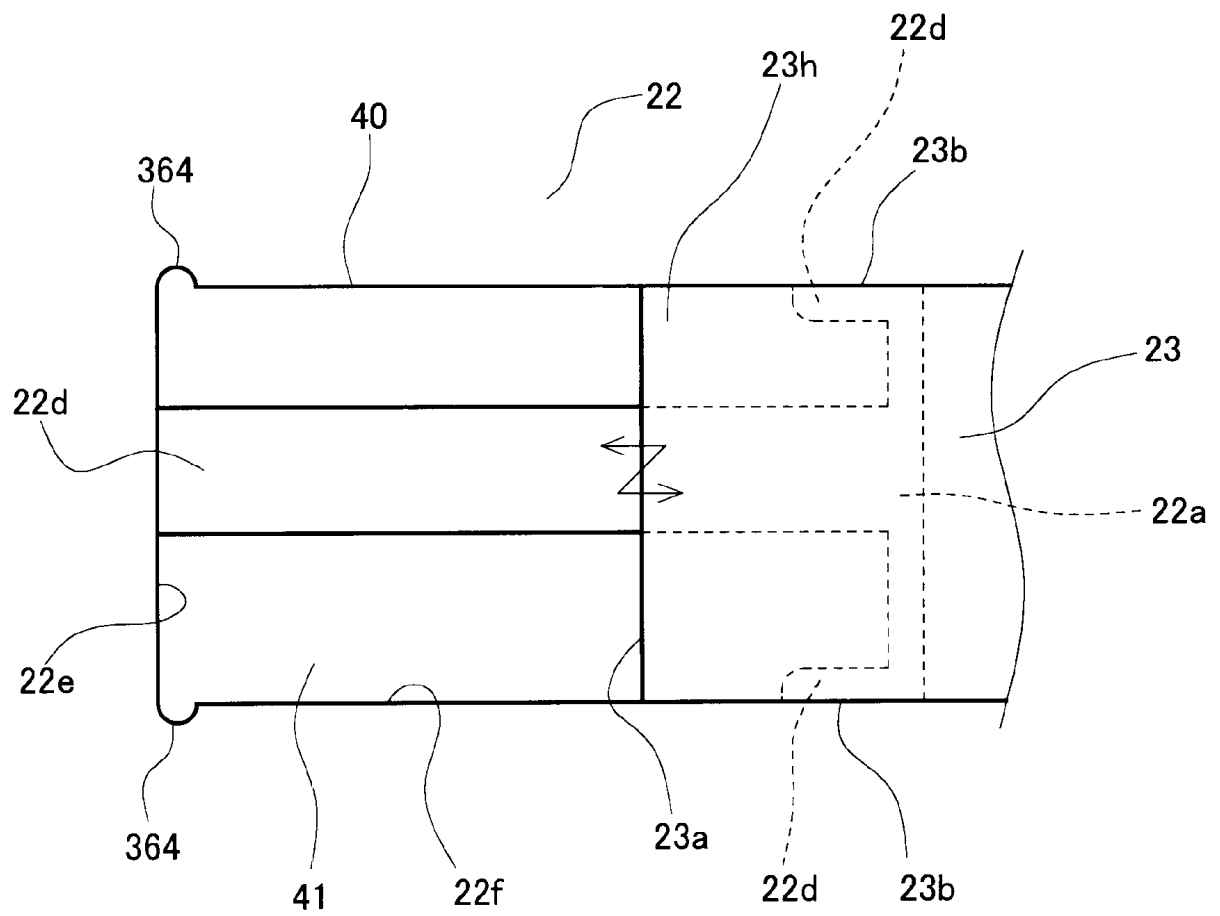


FIG. 3

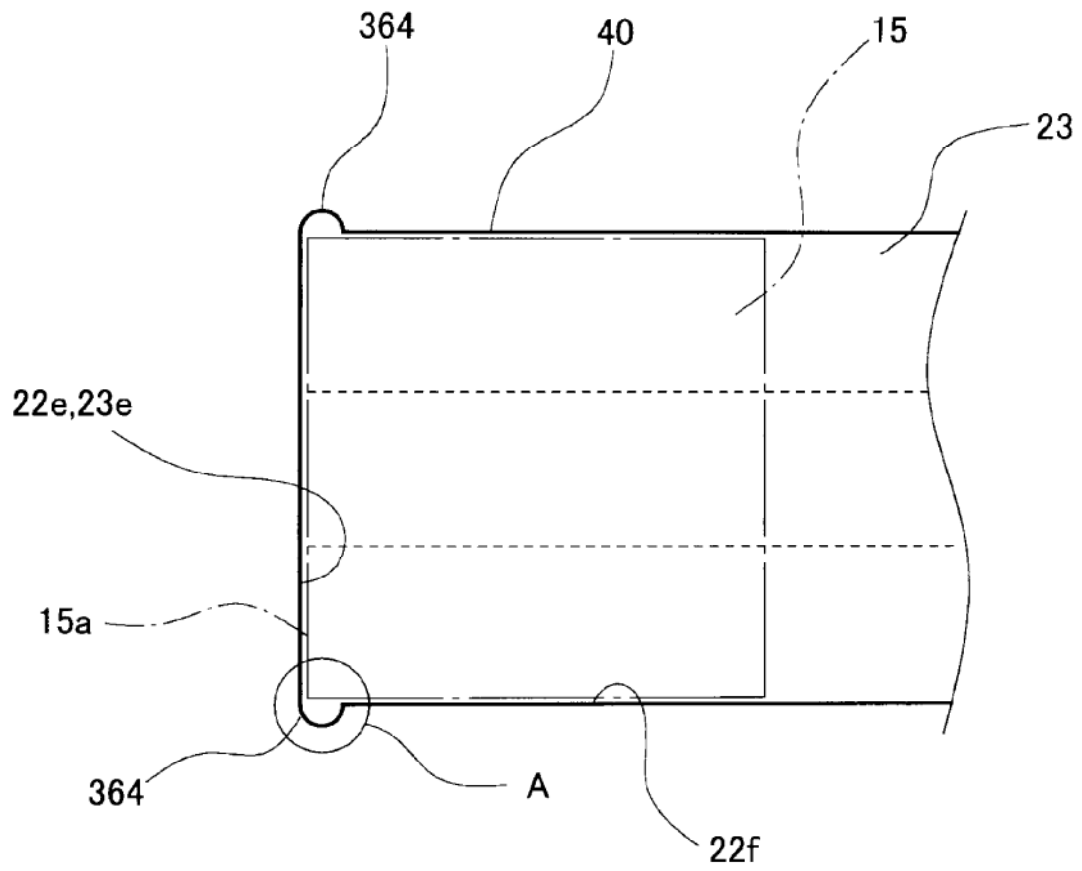


FIG. 4 A

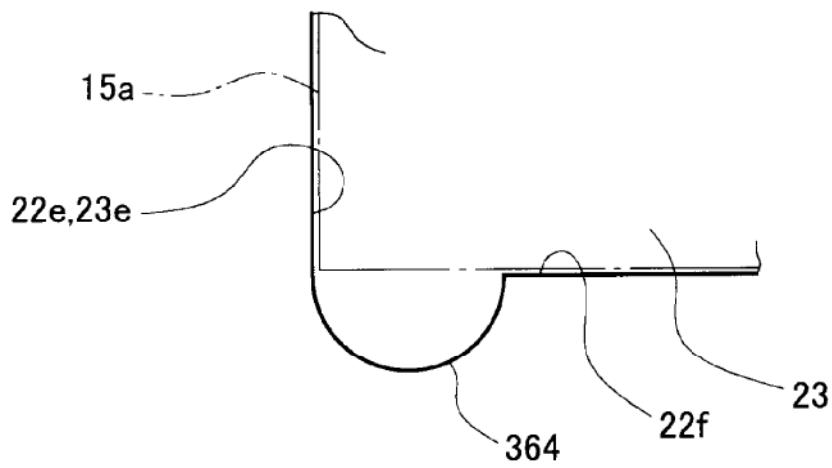


FIG. 4 B

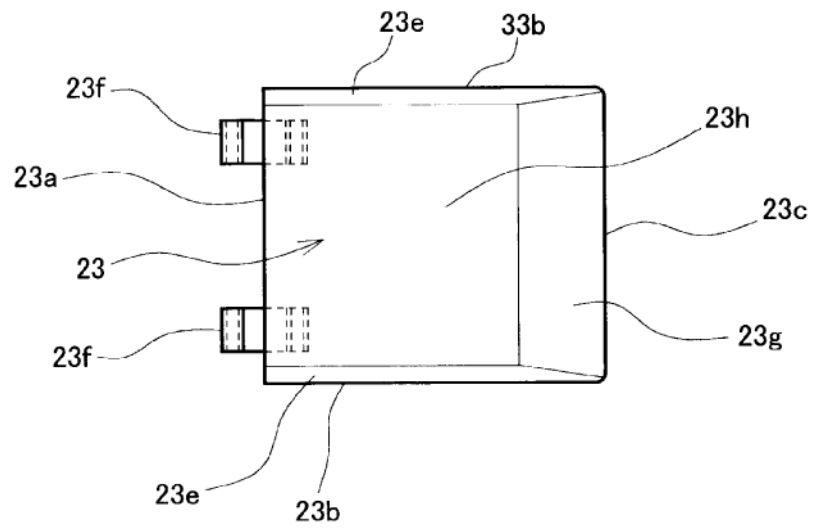


FIG. 5 A

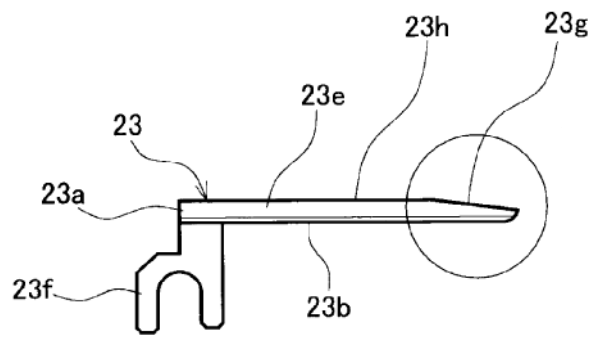


FIG. 5 B

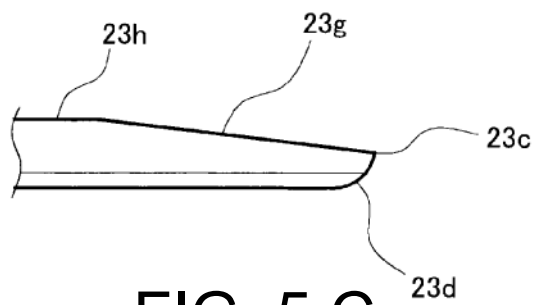


FIG. 5 C

Figure 1 is a cross-sectional view of a substrate 10. The substrate 10 is a thin, horizontal layer. On top of the substrate 10, there is a first layer 11, which is a thin, horizontal layer. On top of the first layer 11, there is a second layer 12, which is a thin, horizontal layer. On top of the second layer 12, there is a third layer 13, which is a thin, horizontal layer. The layers 11, 12, and 13 are stacked on top of each other.

A cross-sectional view of a semiconductor device. It shows a substrate with a gate stack on top. The gate stack includes a gate dielectric layer (14) and a gate electrode layer (15). A trench (12) is formed in the substrate, and a gate electrode (13) is located within the trench.

FIG. 8

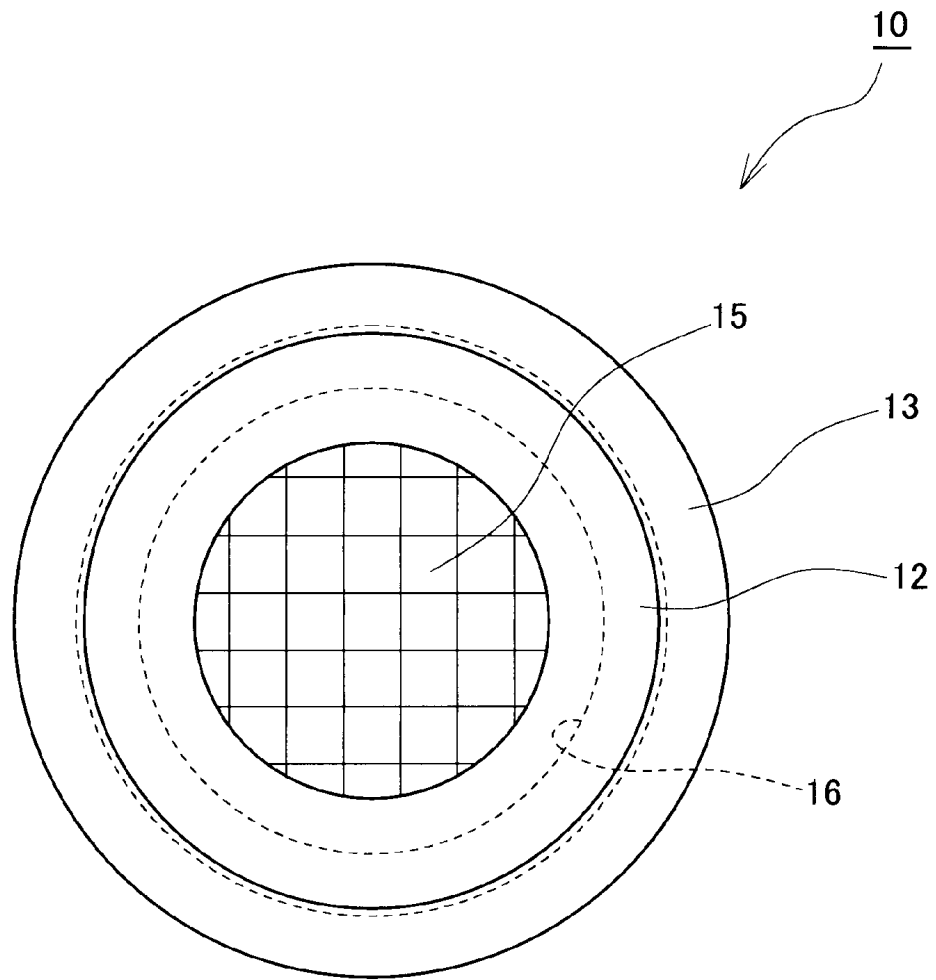


FIG. 9 A

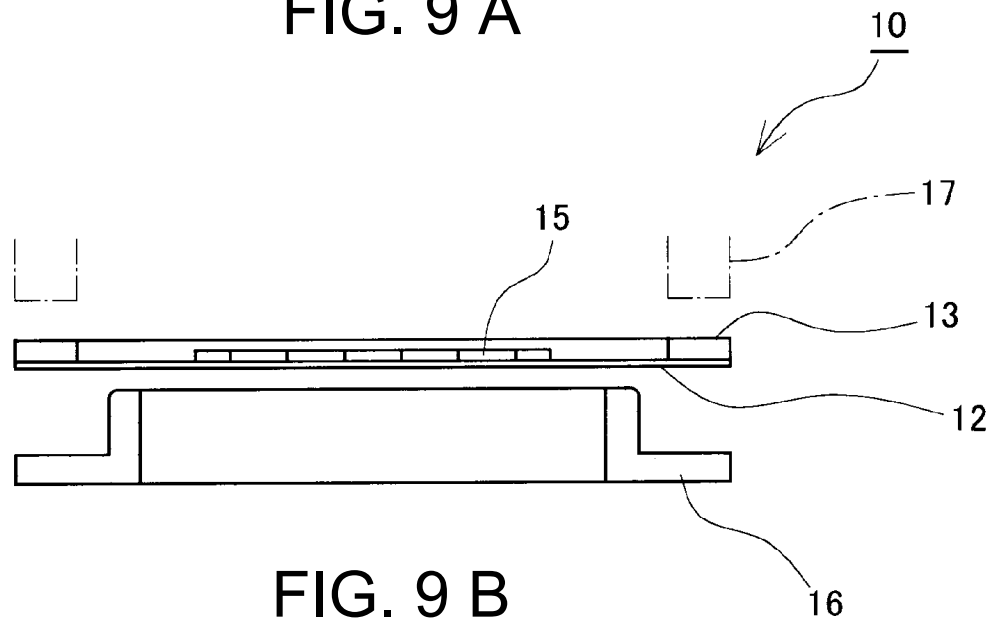
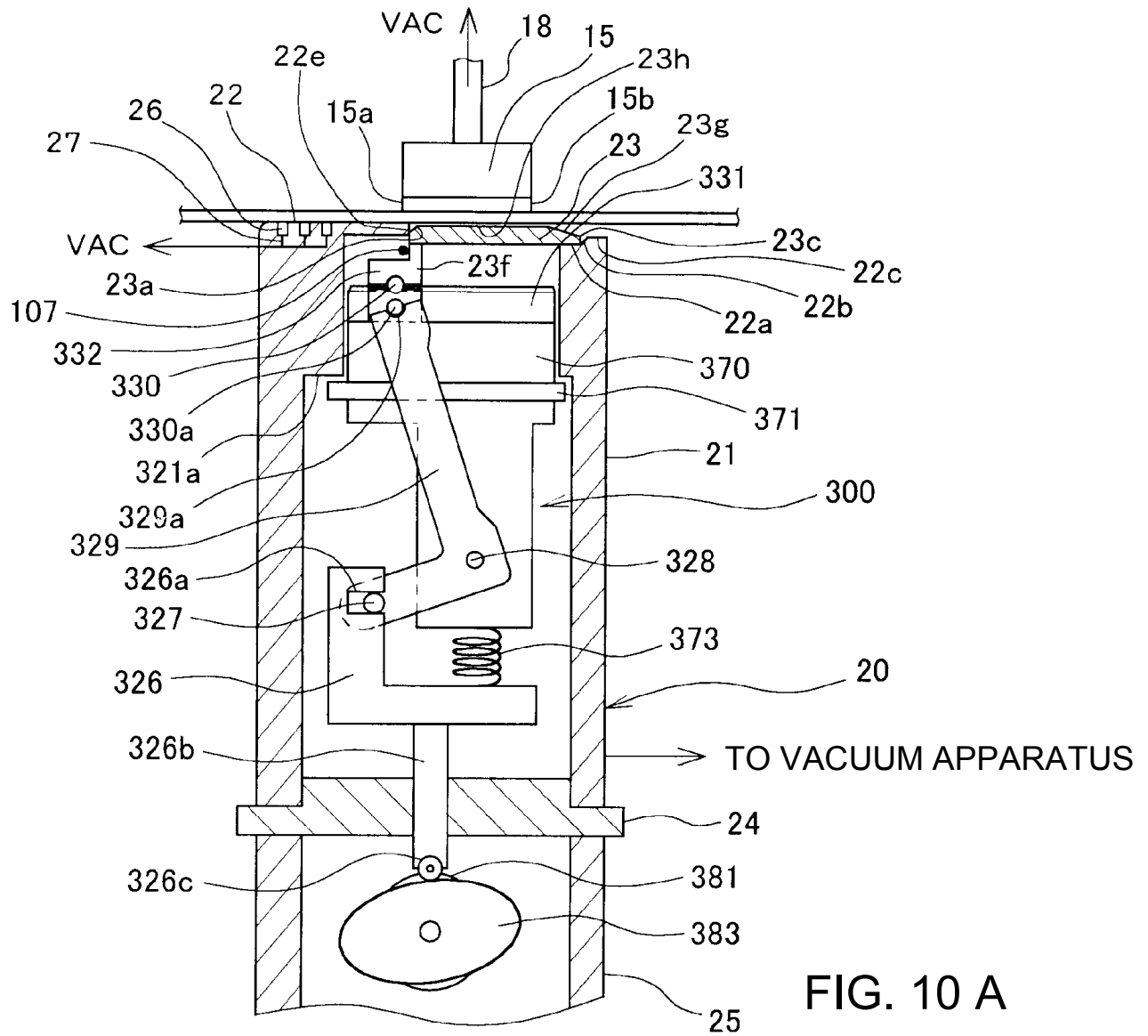
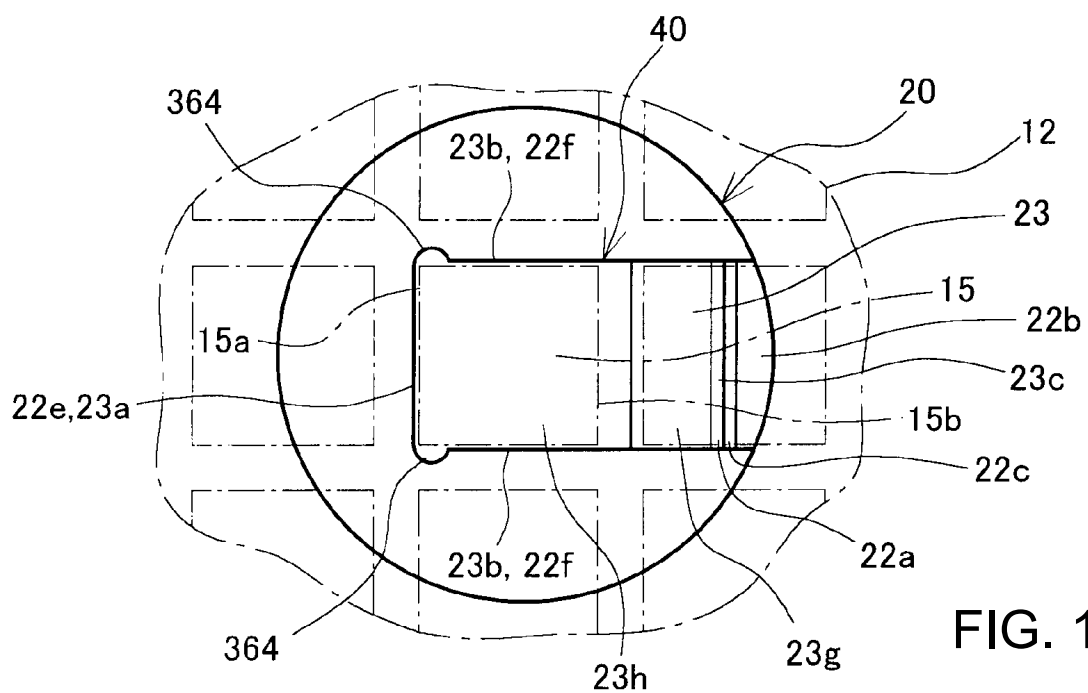


FIG. 9 B



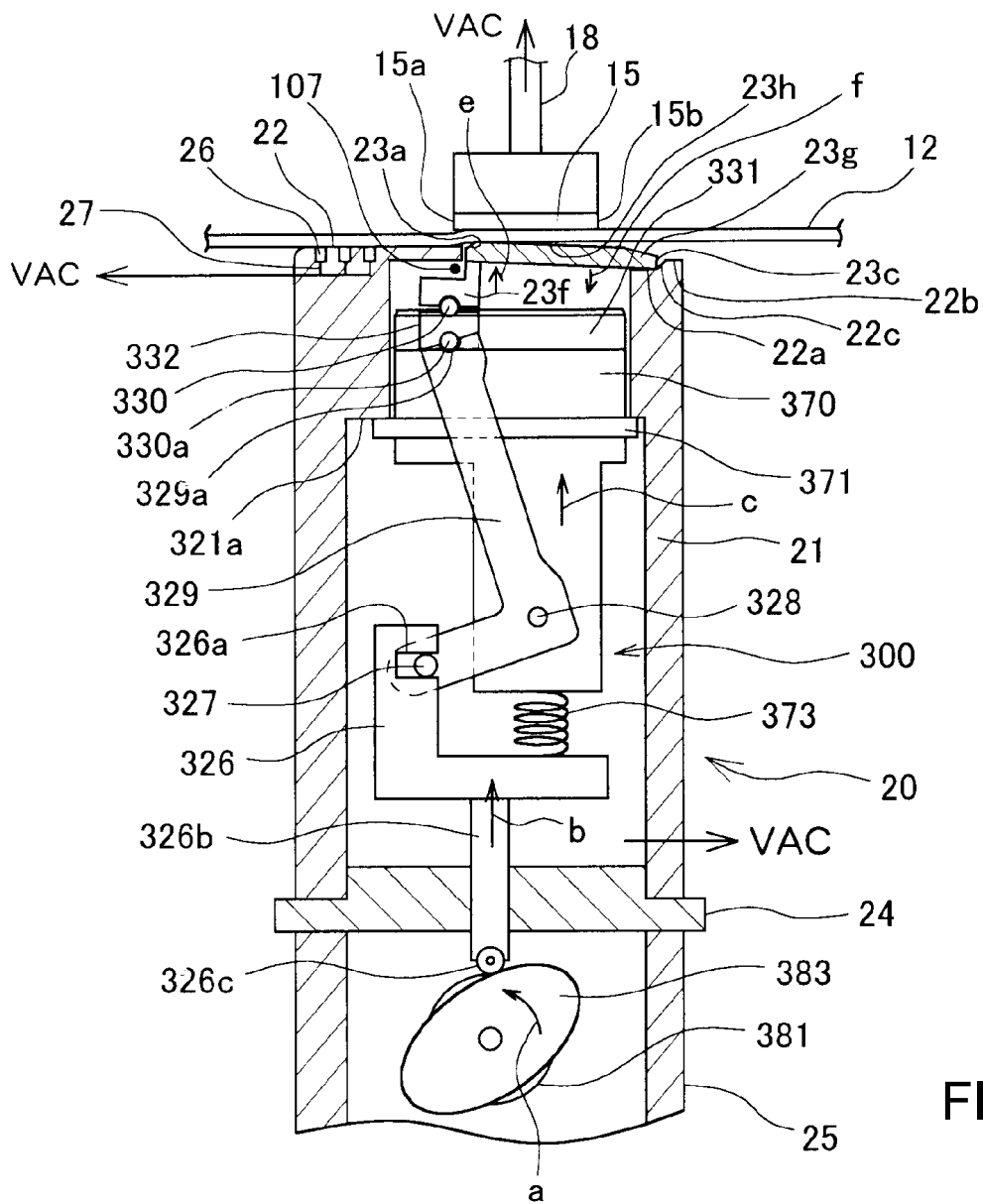


FIG. 12 A

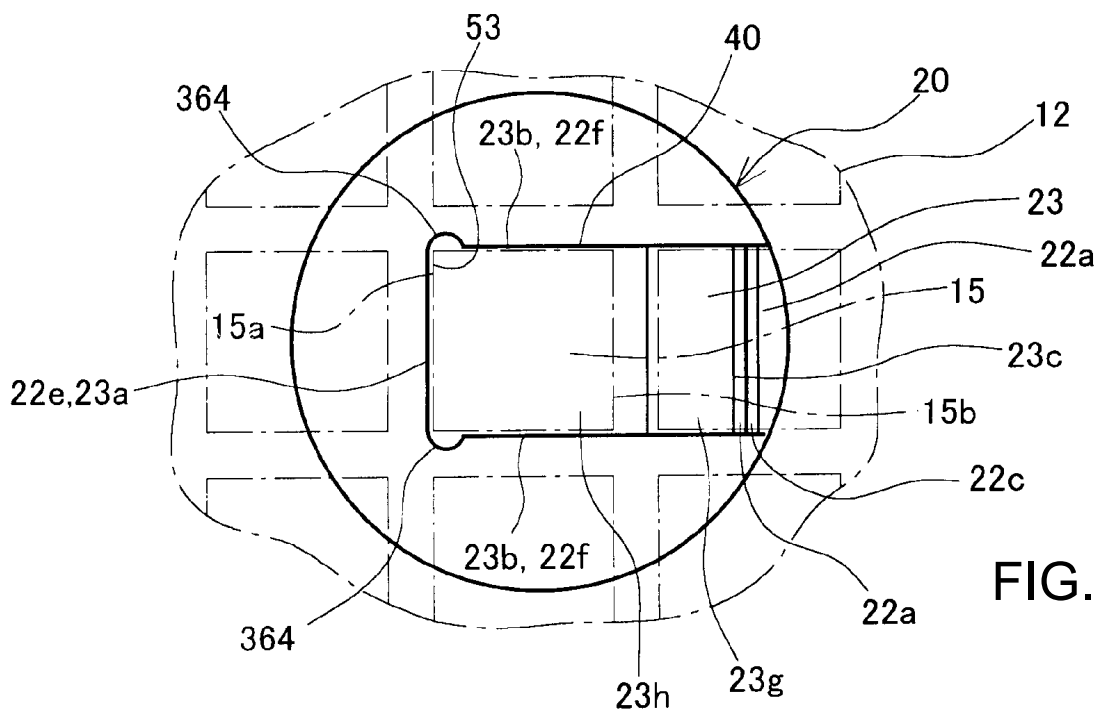


FIG. 12 B

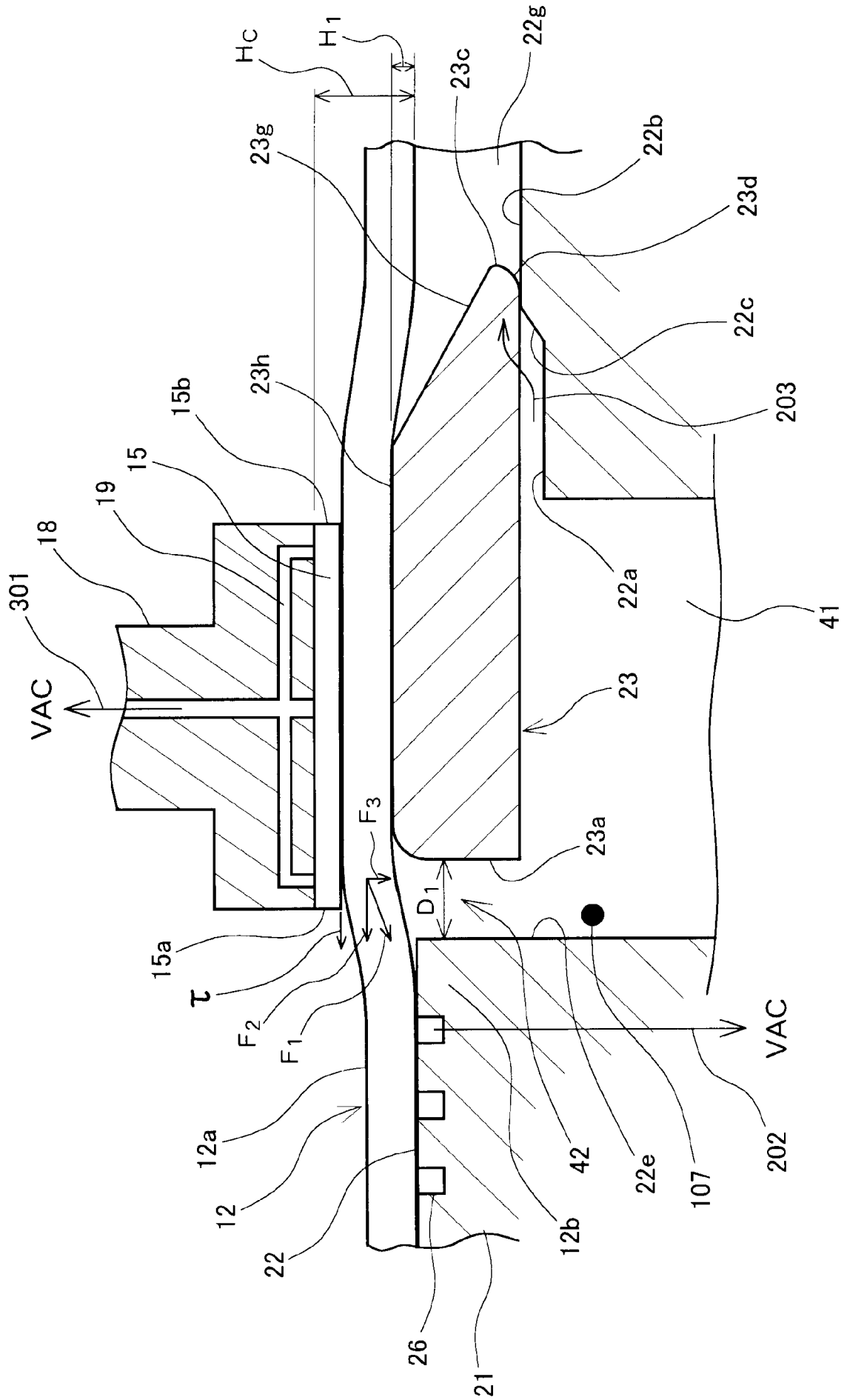


FIG. 14

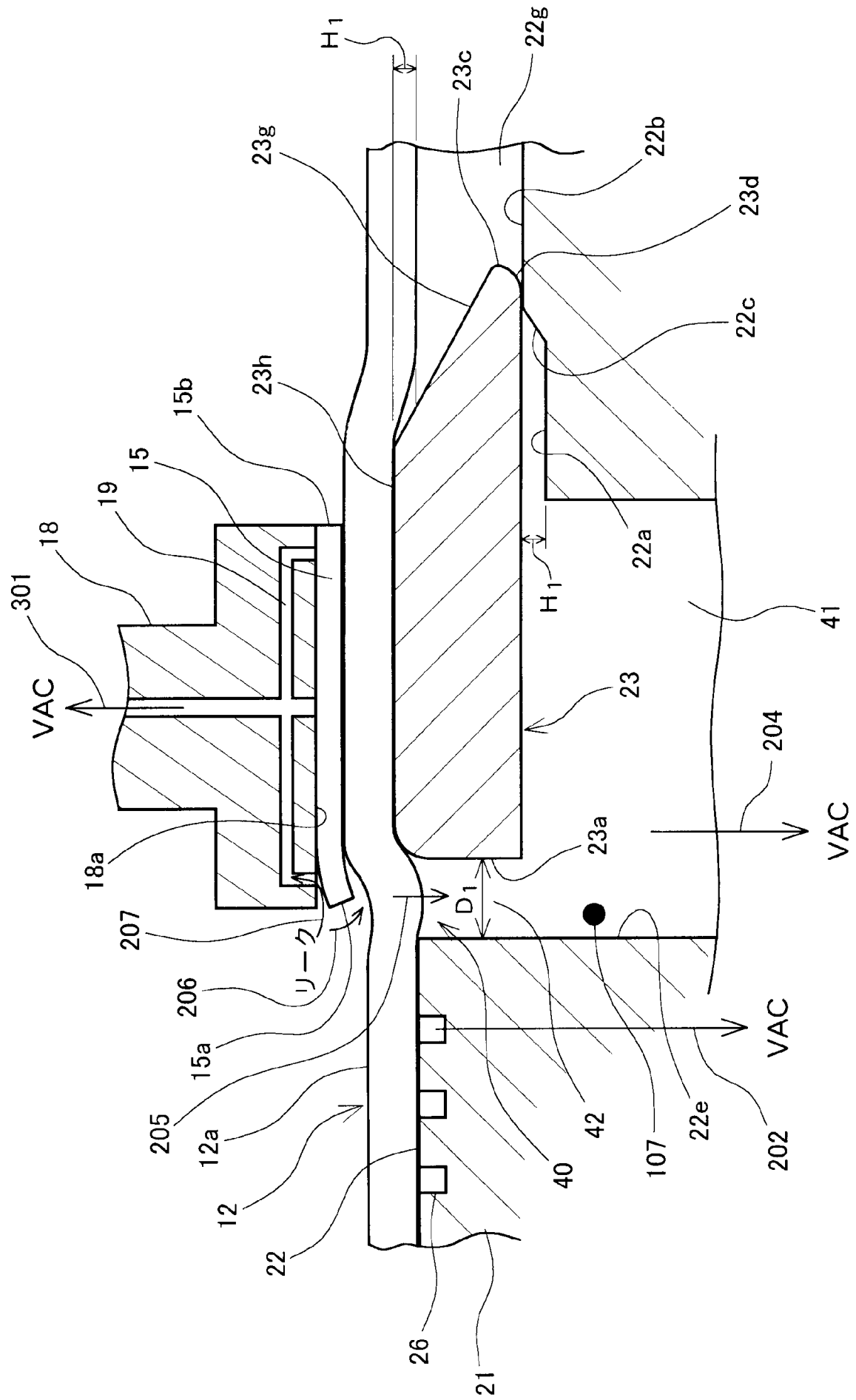


FIG. 15

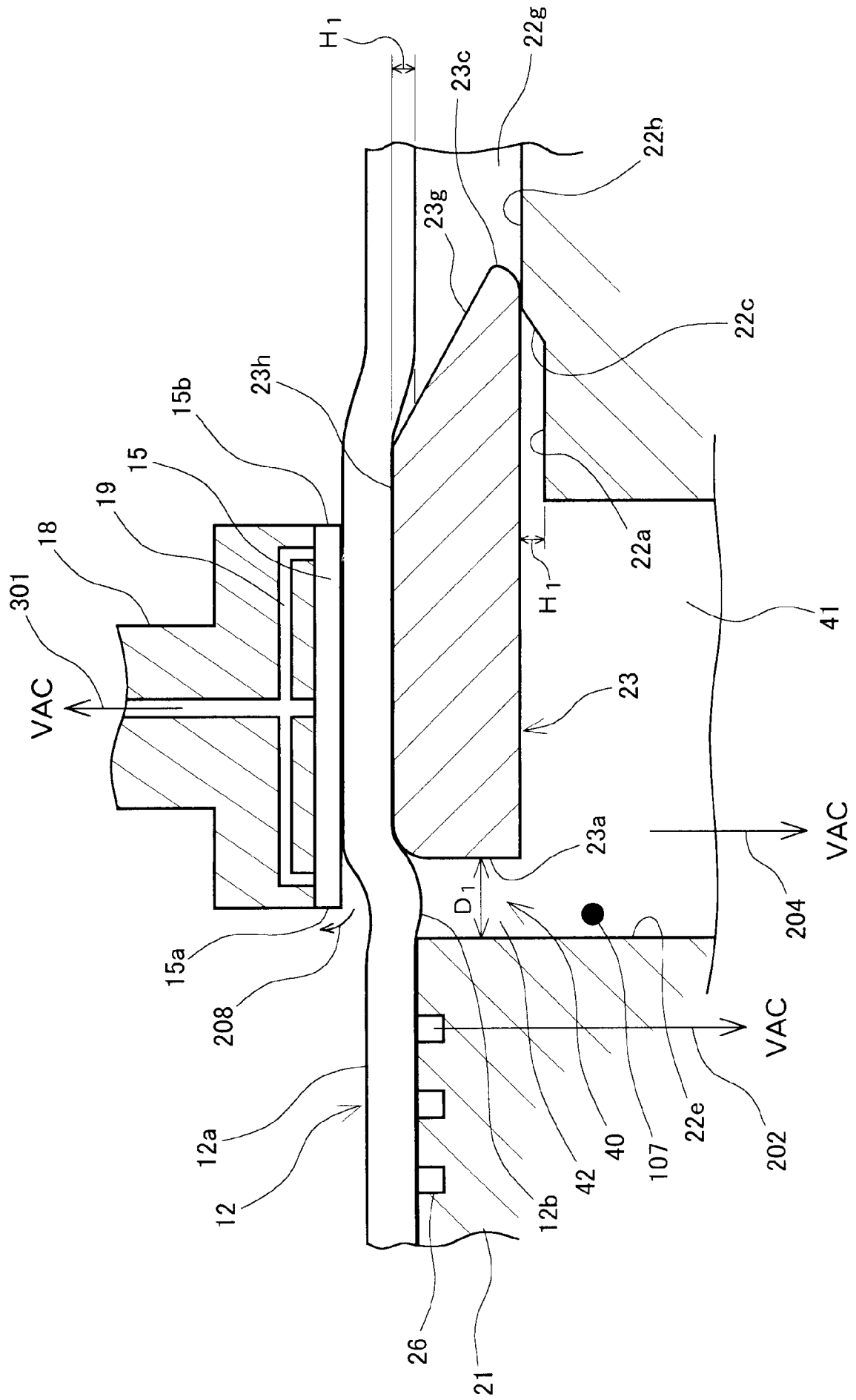


FIG. 16

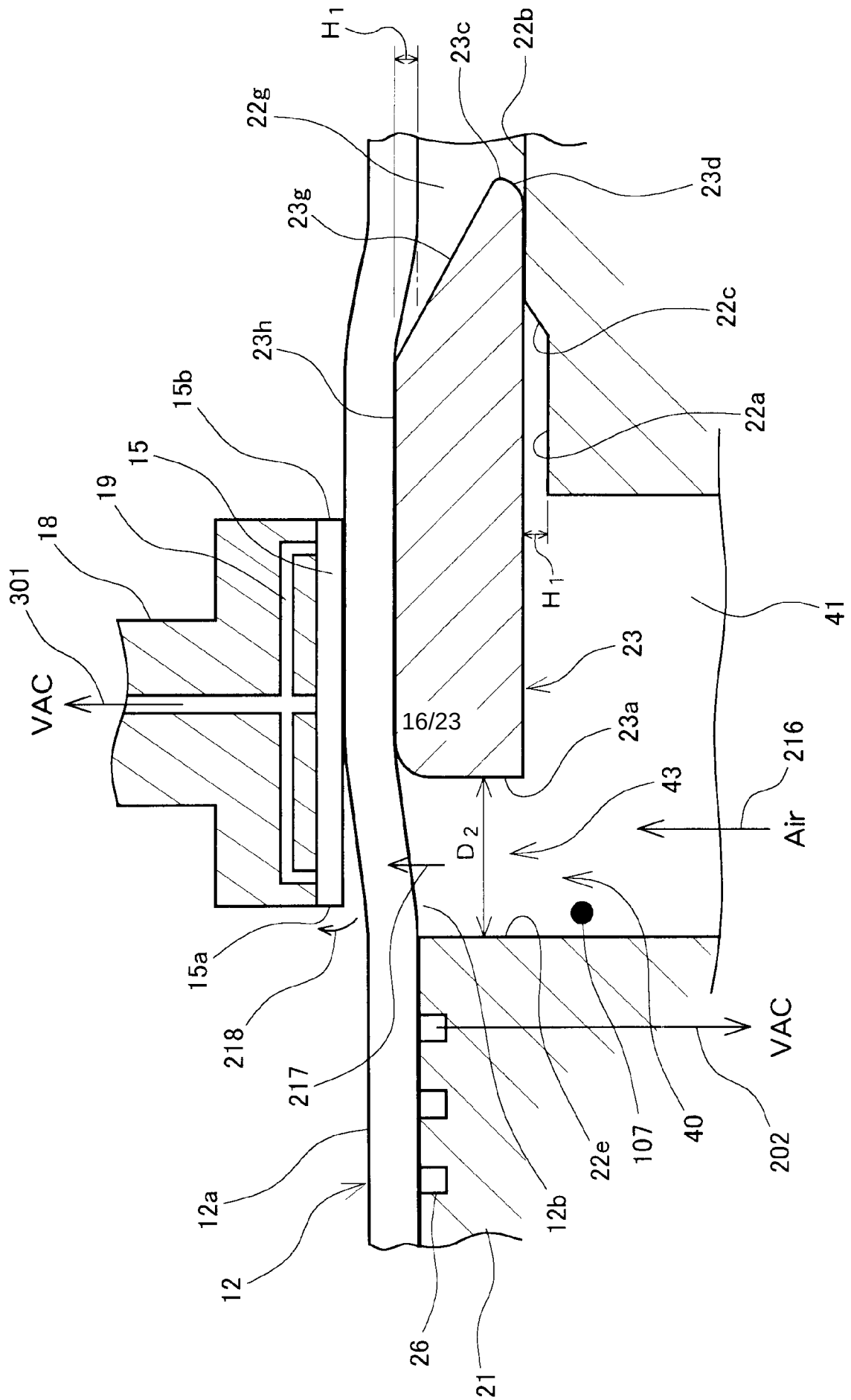


FIG. 19

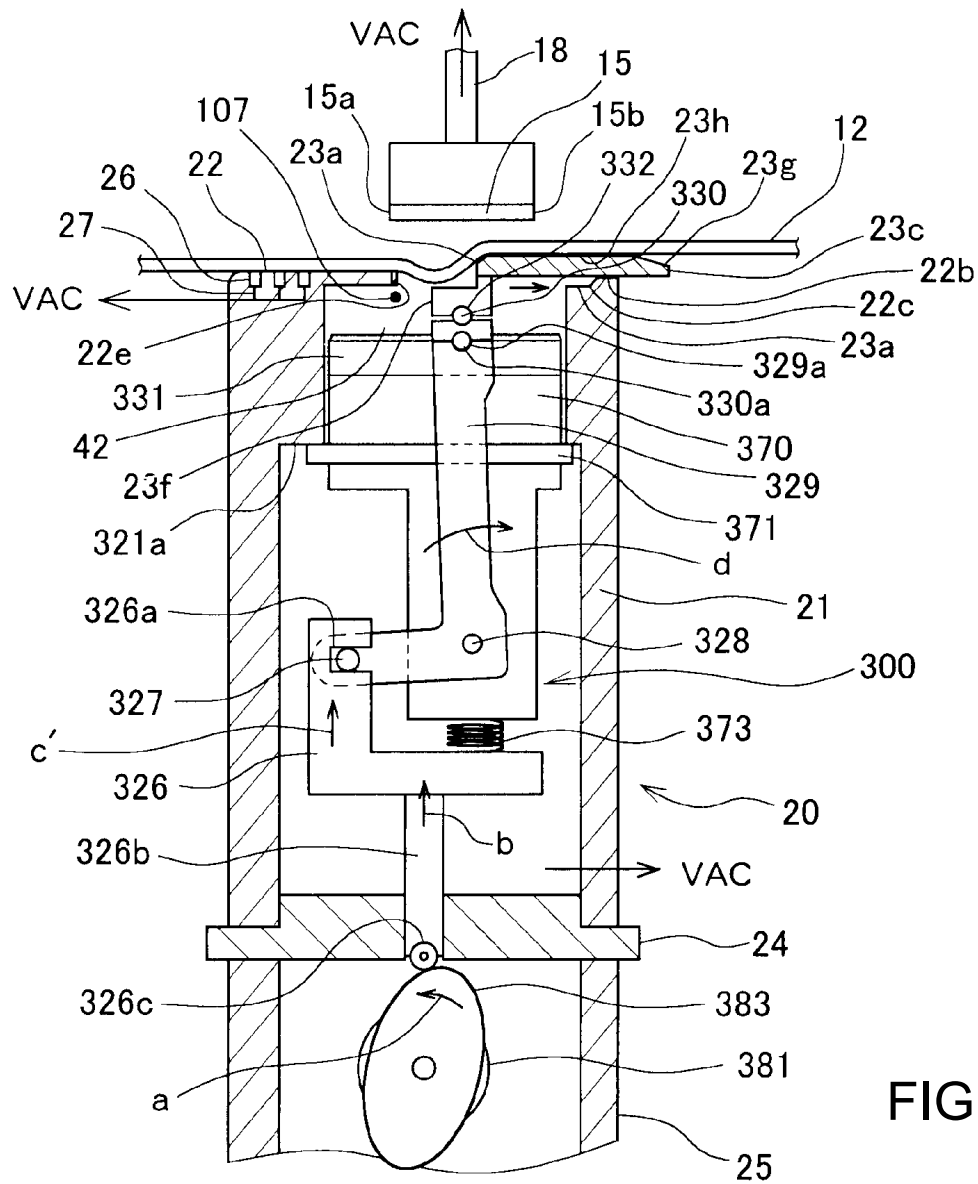


FIG. 22 A

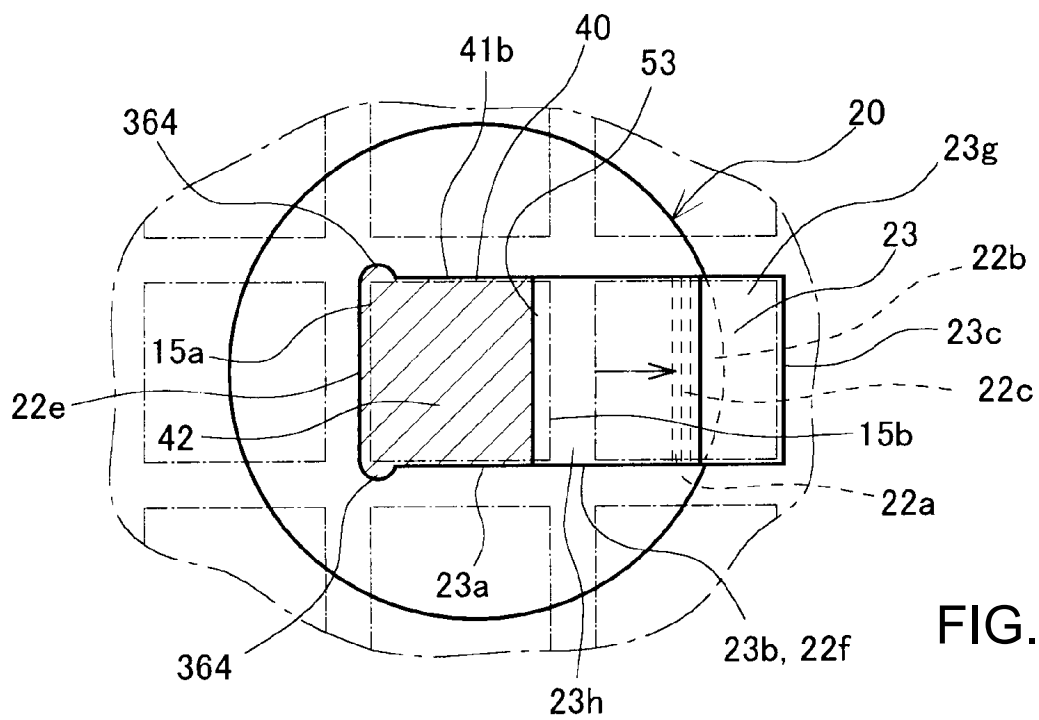
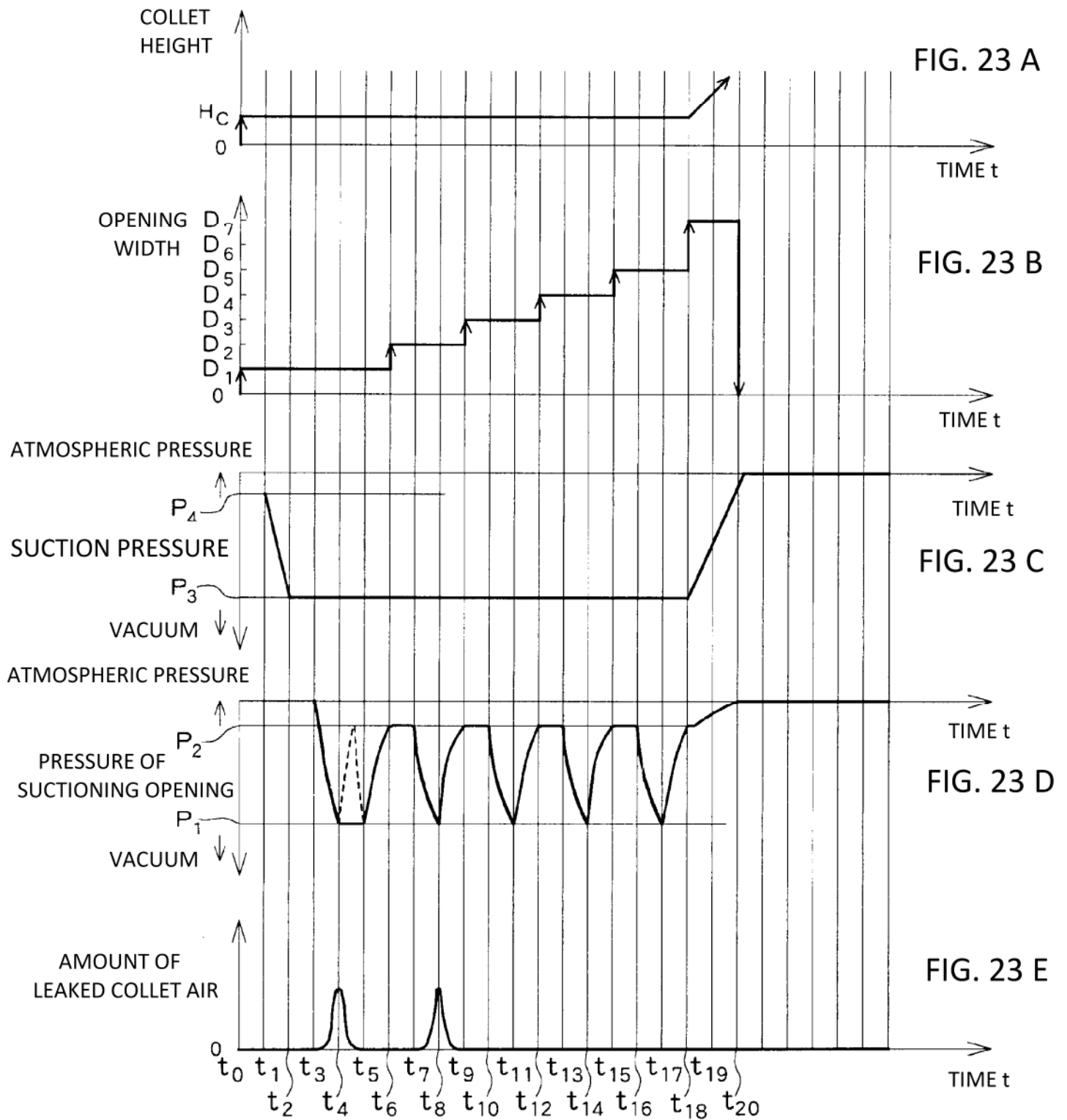


FIG. 22 B



AMOUNT OF
LEAKED COLLET AIR

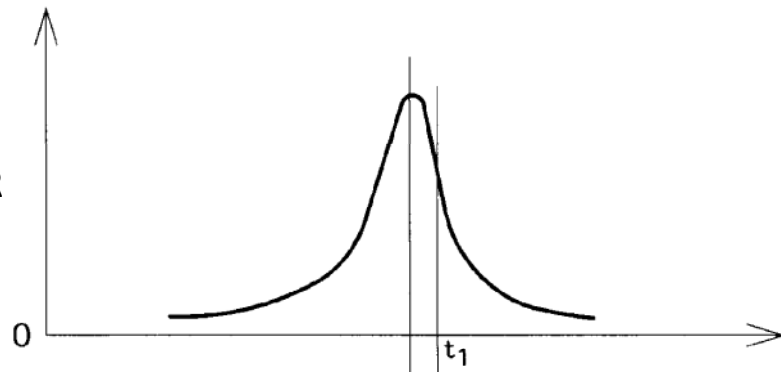


FIG. 24 A

DERIVATIVE VALUE
FOR AMOUNT OF
LEAKED COLLET AIR

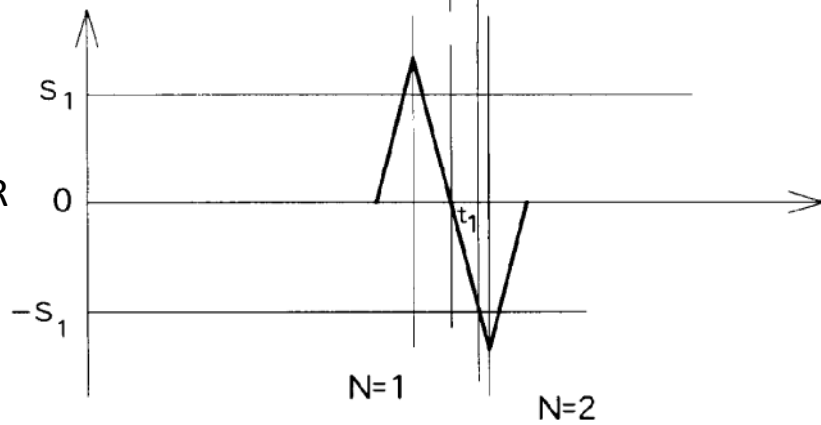


FIG. 24 B

AMOUNT OF
LEAKED COLLET AIR

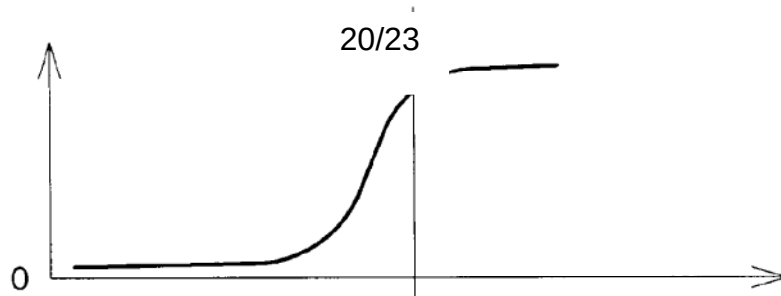


FIG. 24 C

DERIVATIVE VALUE
FOR AMOUNT OF
LEAKED COLLET AIR

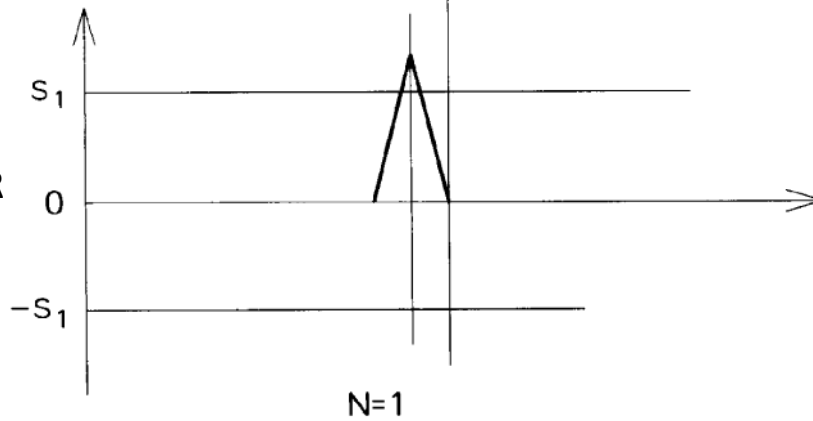


FIG. 24 D

